PROCESS FOR ADJUSTING THE STRAIN ON THE SURFACE OR INSIDE A SUBSTRATE MADE OF A SEMICONDUCTOR MATERIAL

ABSTRACT

This invention relates to a process for adjusting the strain in a strained layer on a substrate. The process steps include identifying one or more regions of the strained layer wherein the strain is to be adjusted; implanting elements into at least one of the regions thus identified in the strained layer; annealing the substrate with the strained layer to a temperature maintained for a sufficiently long time to cure crystalline defects caused by the implantation in the implanted region or regions.

Fig. 1